8013-2323-AU 808nm 1000mW IR Laser Diodes AUTO PACKAGE

Specifications

Device Laser Diode

Package Type TO-5(φ9.0mm)

■Absolute Maximum Ratings(Tc=25℃)

Characteristics		Symbols	Ratings	Units
Reverse Voltage	Reverse Voltag	Po	**1000**	mW
		Vr	**2**	V
Voltage	PIN PD	Vr(PIN)	**10**	V
Operating Temperature		Top	-10 +30	℃
Storage Temperature		Tstg	-40 +85	℃

■Electrical and optical Characteristics(Tc=25℃)

Characteristics		Symbols	Conditions	Min.	Typ.	Max.	Units
Threshold Current		Ith	-	**-**	**300**	**500**	mA
Operating Current		Iop	Po=1000mW	**-**	**1400**	**2000**	mA
Operating Voltage		Vop	Po=1000mW	**-**	**2.1**	**3**	Volts
Slope Efficiency		η	500mW (1000mW)-I(500mW	**0.5**	**0.9**	**1.0**	mW/mA
Monitor Current		Im	Po=1000mW	**0.3**	**1.5**	**6.0**	mA
Beam Divergence (FWHM)	Parallel	θ //	Po=1000mW	**4**	**9**	**17**	deg.
	Prependicular	θ ⊥	Po=1000mW	**20**	**30**	**40**	deg.
Parallel Deviation Angle		Δ θ //	Po=1000mW	**-3**	**-**	**3**	deg.
Perpendicular Deviation Angle		Δ θ ⊥	Po=1000mW	**-3**	**-**	**3**	deg.
Emission Point Accuracy		ΔX	Po=1000mW	**-50**	**-**	**50**	μm
		ΔY	Po=1000mW	**-50**	**-**	**50**	μm
		ΔZ	Po=1000mW	**-50**	**-**	**50**	μm
Lasing Wavelength		λ	Po=1000mW	**804**	**807**	**810**	nm

Im is sorting by custom's need

◎θ // and θ ⊥ are defined as the angle within which the intensity is 50% of the peak value.